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Updated: 27 February 2014 **CORRIGENDUM:** A novel wavelength-adjusting method in InGaN-based lightemitting diodes

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The details for affiliations 1 and 2 were incomplete in the original HTML and PDF versions of this Article. The affiliations were incorrectly listed as "¹Key Laboratory for Renewable Energy, Chinese Academy of Sciences, Beijing 100190, China" and "²Beijing Key Laboratory for New Energy Materials and Devices, Beijing 100190, China". The correct affiliations are listed above. These have now been corrected in the HTML and PDF versions of the Article.